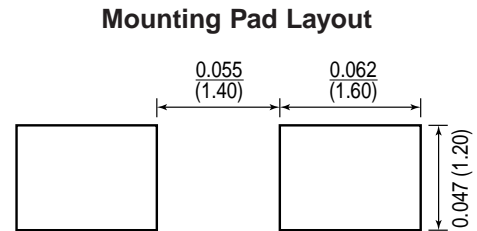
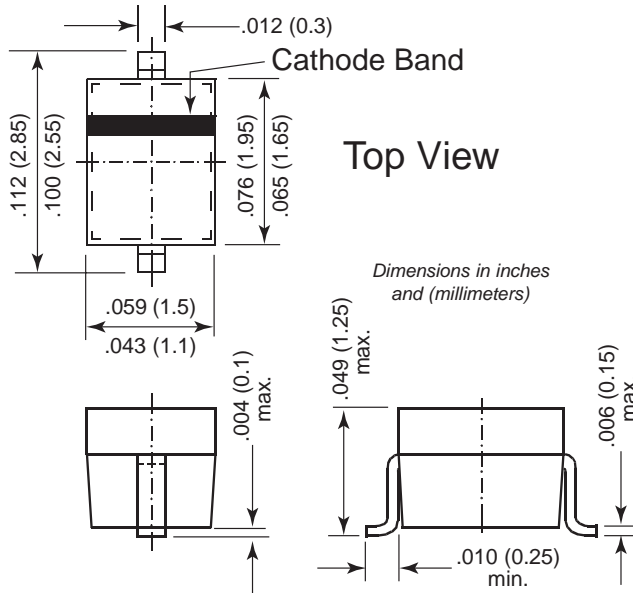


## High-Voltage Small-Signal Switching Diode


**SOD-323**


### Mechanical Data

**Case:** SOD-323 Plastic Package

**Weight:** approx. 0.004g

**Marking Code:** B6

**Packaging Codes/Options:**

D5/10K per 13" reel (8mm tape), 30K/box

D6/3K per 7" reel (8mm tape), 30K/box

### Features

- Silicon Epitaxial Planar Diode
- Fast switching diode, especially suited for applications requiring high voltage capability

### Maximum Ratings and Thermal Characteristics

 $T_A = 25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	$V_R$	240	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	300	V
Peak Repetitive Reverse Current	$I_{RRM}$	200	mA
Forward Current (continuous)	$I_F$	225	mA
Peak Repetitive Forward Current	$I_{FRM}$	625	mA
Non-Repetitive Peak Forward Current at $t_p = 1\mu\text{s}$ at $t_p = 1\text{s}$	$I_{FSM}$	4.0 1.0	A
Power Dissipation	$P_{tot}$	200 <sup>(1)</sup>	mW
Typical Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	650 <sup>(1)</sup>	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-65 to +150	$^\circ\text{C}$

**Note:** (1) Device on Fiberglass Substrate, see layout on second page

## Electrical Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{BR}$	$I_R = 100\mu\text{A}$	300	—	—	V
Leakage Current	$I_R$	$V_R = 240\text{V}$ $V_R = 240\text{V}, T_J = 150^\circ\text{C}$	— —	— —	100 100	nA $\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 20\text{mA}$ $I_F = 100\text{mA}$	— —	0.83 —	0.87 1.00	V
Capacitance	$C_{tot}$	$V_F = V_R = 0$ $f = 1\text{MHz}$	—	—	5.0	pF
Reverse Recovery Time	$t_{rr}$	$I_F = I_A = 30\text{mA}$ $I_{rr} = 3.0\text{mA}, R_L = 100\Omega$	—	—	50	ns

**Note:**

(1 )Device on fiberglass substrate, see layout